CF4 Etching Protocol

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Prep

1. Coat protective layer of Shipley on back of wafer
2. Spin coat rate: 1000 rpm, 15 sec
3. Bake: 120°C, 1 min
4. Pattern Other side
5. Spin coat rate: 1000 rpm, 15 sec
6. Bake: 120 °C, 1 min

CF4 Etch

1. Turn on Plasma Etcher
2. Vac On
3. Vent Off
4. Pump Down to **500 mT**
5. Turn on Gas 2
6. Pump down to 550mT
7. Turn on power
8. Adjust Power to 100W
9. Adjust Gas so that Press is about 600 mT
10. Etch for 6-10 min
11. Turn off power
12. Turn off gas
13. Vac off
14. Vent On

Plasma Etcher.

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